

Magnetic field effects on non-periodic superlattice structures

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A simple numerical method to study the effect of an applied magnetic field on the energy spectrum of non-periodic superlattice structures is presented. The magnetic field could be either parallel or perpendicular to the growth direction. Our method is based on the transfer matrix technique and on the effective mass approximation. We discuss the advantages and disadvantages of the proposed approach using several examples. In particular, we study the perturbation to the energy spectrum of periodic superlattice induced by the introduction of an enlarged well. We found that these perturbations are negligible for $B//z$ but relevant for $B\perp z$. Preliminary results for Fibonacci superlattices in magnetic fields are presented as well. In these quasi-periodic structures the energy levels become strongly dispersive in presence of a perpendicular magnetic field.

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I. INTRODUCTION

In 1970, Tsu and Esaki proposed superlattices as new structures with peculiar properties (minibands) which allowed new physical phenomena to be studied. [1] In recent years, the improvement of epitaxial growth techniques renders disposable samples to study the properties of transport in the vertical direction (i. e. parallel to the growth direction, z). Resonant quantum tunneling through double barrier heterostructures, transport along superlattice minibands, and optical studies in biased multiquantum well structures have recently attracted great attention. [2] In short period superlattices, the coupling between adjacent wells leads to transport through superlattice miniband states. [3] In addition, the present availability of high magnetic fields stimulated many experimental studies of magnetotransport. [4] A problem of increasing interest is the effect of a transverse magnetic field, B , on the tunneling through a barrier separating either two semiconductors [5] or two superlattices [6]. Magnetotransport in transverse fields has also been studied in a semiclassical macroscopic framework [7]. Other topics concern the effect of an applied magnetic field perpendicular to the semiconductor layers of an heterostructure [8,9]. In this case, the magnetic quantization in the layer plane collapses the two-dimensional (2D) electron gas in

a discrete set of cyclotron orbits of zero degrees of freedom (0D system).

The problem of the influence of an external magnetic field on the superlattice energy levels have been throughout studied by theoretical techniques. Two different approaches have been used: the first is based on a numerical integration either of the Schrödinger equation [10] or of a reduced Luttinger Hamiltonian [11] and the second solves the Schrödinger equation using the method of expansion of the solutions in series of analytical functions (like sine functions [12], hypergeometrical confluent functions [13] or parabolic cylinder functions [14]). In this paper we propose a different approach based on the extension of the well-known Transfer Matrix (TM) method [15,16] to superlattices in magnetic field. The interest in our approach is the possibility to study superlattices formed by whatever a succession of layers. The TM method has been widely used to solve the problem of non-periodic structures. [17] Its simplicity is related to the use of the product of only 2x2 matrices. This renders the method very appealing because it is easily implementable on small computers.

In the Appendix we present the details of our approach to the Transfer Matrix method in absence of magnetic field. For simplicity we have restricted our discussion to the electronic problem, i. e. we neglect the holes. In section II we study the case of $B||z$, where z is the growth direction: the superlattice miniband width is varied due to the magnetic quantization in the heterostructure layer planes, i.e., to the conservation of the Landau level index along the different layers. In section III, we analyzed the case of $B\perp z$. A new equation which couples the motion in the layer plane and in the vertical direction should be solved to obtain the energy levels. Then, we study two particular problems: the enlarged well in a superlattice (section IV) due to its importance for vertical transport studies and the Fibonacci superlattice (section VI) as an example of non-periodic superlattice. In section V we have computed the density of states for magnetic fields oriented either parallel or perpendicular to z . Finally, section VII ends the paper with a summary of the main results.

II. MAGNETIC FIELD PARALLEL TO Z

Through the effective-mass approximation it is possible to separate the electronic wavefunction in a component (usually assumed to be a plane wave) for the motion in the layer plane and in a component (solution of the equation (11)) for the motion in the z direction. A magnetic field applied in the z direction does not introduce a mixing of the parallel and the perpendicular electron wave functions. However, it changes the plane waves for the motion in the layer plane into harmonic oscillator wave functions and it collapses the free electron dispersion relation in a discrete set of Landau levels. [9] In this case, the eigenvalues E_n are

$$E_n = E_z + \hbar\omega_w(n + 1/2) \quad (1)$$

with $n = 0, 1, 2, \dots$ the Landau level number, E_z the eigenvalue for the motion in the vertical direction, $\omega_w = eB/m^*c$ the cyclotron frequency for the GaAs effective-mass m^* , e the electronic charge and c the light velocity in vacuum. In (1), we have neglected the spin magnetic energy. [18]

To obtain E_z , it is necessary to solve the effective-mass Schrödinger equation

$$\left[-\frac{\hbar^2}{2m^*} \nabla^2 + V_n(B, z) \right] \psi(z) = E_z \psi(z) \quad (2)$$

where the magnetic field is included by changing the ordinary superlattice potential, $V_{SL}(z)$, with an effective one-dimensional potential, $V_n(B, z)$, different for each Landau level n ,

$$V_n(B, z) = V_{SL}(z) + \hbar(n + 1/2)[\omega_w - \omega_b] = V_o + \hbar(n + 1/2)[\omega_w - \omega_b] \quad (3)$$

in the $\text{Al}_x\text{Ga}_{1-x}\text{As}$ barriers and

$$V_n(B, z) = V_{SL}(z) = 0 \quad (4)$$

in the GaAs wells. V_o is the conduction band discontinuity between GaAs and $\text{Al}_x\text{Ga}_{1-x}\text{As}$, and ω_b is the cyclotron frequency for the $\text{Al}_x\text{Ga}_{1-x}\text{As}$ effective-mass. The potential described in equations (3) and (4) reflects the conservation of the Landau level number through the layers. [8] Consequently, E_z depends on the applied magnetic field.

Figure 1 shows the highest and lowest electron energy level of the miniband of a 30/30 superlattice (30Å thick wells and barriers, with $x = 0.33$ in the barriers) versus the applied magnetic field for different values of n . [19] By increasing the applied magnetic field, the electron energy levels move to low energy. The energy shift is larger for higher Landau level number. This effect is explained by equation (3). The $\text{Al}_x\text{Ga}_{1-x}\text{As}$ effective mass is higher than the GaAs effective mass, so that the cyclotron frequency in the $\text{Al}_x\text{Ga}_{1-x}\text{As}$ layers is lower than in the GaAs layers. Thus, the second part on the right hand side of equation (3) is a negative term proportional to B and n . If B or n increases, the potential barrier is lowered, and the electron energy levels are shifted to lower energies. Hence, the coupling of the electron wave functions in adjacent wells is augmented increasing the miniband width. To evaluate this effect, we compare the dependence of E_z on B for various n with the corresponding cyclotronic kinetic energy $\hbar\omega_w(n + 1/2)$. For B measured in Tesla, $\hbar\omega_w = 1.72 B$ meV. So that the conservation of the quantum number n changes E_n by 5 %. This effect could be increased if a higher aluminum concentration is used.

III. MAGNETIC FIELD PERPENDICULAR TO Z

In this case, the Hamiltonian describes a spinless particle in a layer of the superlattice, with an effective mass m^* and charge e , subject to a constant and uniform transverse magnetic field $\mathbf{B}$, i.e.

$$H = \frac{1}{2m^*}(\mathbf{p} - \frac{e}{c}\mathbf{A})^2 + V_{SL}(z) \quad (5)$$

where $\mathbf{p} = -i\hbar\nabla$, and $\mathbf{A}$ is the magnetic vector potential. We fix the direction $B||x$ to simplify the equations. The Hamiltonian takes the form [9]

$$H = -\frac{\hbar^2}{2m^*}\nabla^2 + \frac{e^2 B^2 z^2}{2m^* c^2} - \frac{ie\hbar B z}{m^* c} \frac{\partial}{\partial y} + V_{SL}(z) \quad (6)$$

where the *gauge* $\mathbf{A} = (0, -Bz, 0)$ has been used. By using a plane wave in the x and y direction and neglecting spin effects, it is possible to find the envelope wave-function $\psi(z)$ that describes the motion of the carriers along the z direction of the heterostructure through the equation

$$H\psi(z) = E\psi(z) \quad (7)$$

with E the electron energy and the effective mass Hamiltonian, H , given by

$$H = -\frac{\hbar^2}{2m^*} \frac{d^2}{dz^2} + \frac{1}{2}m^*\omega_w^2(z - z_0)^2 + V_{SL}(z) = -\frac{\hbar^2}{2m^*} \frac{d^2}{dz^2} + V_{eff}(z) \quad (8)$$

where the definitions $z_0 = -\hbar k_y c / eB$ have been used. k_y is the wave-vector in the y-direction. Note that the eigenvalues E depend on z_0 .

To calculate the electron energy eigenvalues for different z_0 (dispersion relation) we have assumed a flat band approximation for the potential $V_{eff}(z)$. This consists in taking $V_{eff}(z)$ constant in each layer. For a layer i between two interfaces z_j and z_{j+1} , we chose a mean value for the magnetic potential. We define $z_i = (z_j + z_{j+1})/2$ and the second term on the right hand side of equation (8) yields a constant value $V_i = m^*\omega_w^2(z_i - z_0)^2/2$. Then, in order to use the transfer matrix method, we substitute $E \rightarrow E - V_i$ in each formula of the Appendix. This approximation is based on the large number of barriers and wells that forms a superlattice. The averaged flat band potential is expected to be a good approximation of the real potential $V_{eff}(z)$ if the wave function extends over many wells and barriers. In this case, we can neglect the parabolic shape of the potential $V_{eff}(z)$ in each individual well and barrier. Increasing the number of layers, the accuracy of the averaged flat band approximation is increased. In this way, the application of a parabolic magnetic field on a superlattice is modeled by means of a variable height flat band potential. This method is similar to the approximations that R. Tsu and L. Esaki have used to compute the effect of an external electric field on a superlattice. [20]

Our approximation has a low influence for low magnetic fields. In addition, we have found a very small numerical differences for the dispersion relations of electrons in superlattice under high magnetic fields (up to $B=20T$) with respect to the results of J.C. Maan [10]. In Ref. [10] the Schrödinger equation (8) has been numerically integrated. Moreover, to check further the approximation used in our calculations we have tried to reproduce more accurately the potential $V_{eff}(z)$ in each layers. In a barrier or well placed between the z_j and z_{j+1} interfaces we discretize the layer in a finite number (L) of regions. The interfaces between the new L regions are found at $z_\ell = z_j + (z_{j+1} - z_j)\ell/L$. We define a flat band potential in each ℓ region as $V_\ell = V_{SL}(z_\ell) + m^*\omega_w^2(z_\ell - z_0)^2/2$. Increasing the number L , the new step-like potential will be closer and closer to $V_{eff}(z)$. Table I reports the electron energy levels in a 30/30 $Al_{0.33}Ga_{0.67}As$ -GaAs superlattice with $B = 5T$ for different L values and a fixed z_0 . Including a large number of quantum wells in the superlattice (20 wells) the energy levels obtained with $L = 2, 3, \dots$ are slightly different from the results with $L = 1$. The $L = 1$ case represents a very good compromise between computational efficiency and the accuracy of the results. For $L \neq 1$ the number of the matrix products are changed from $N - 1$ (N is the number of layers) to $(N - 1)L$.

We have plotted in Fig. 2 and 3 the calculated electron dispersion relations (z_0 versus E) using 20 wells and $L = 1$ for a 30/30 and 60/60 superlattices at $B = 5T$ and $4T$, respectively. These are representative of two electronic dispersion relations with one miniband (30/30 superlattice) or two minibands (60/60 superlattice). The dispersion relation is flat if the eigenvalues belong to the minibands calculated in absence of magnetic field and it is almost parabolic if not. [10] Anti-crossing in the energy levels occurs for several z_0 values. For the 60/60 superlattice, it is found that the anticrossing occurs also between the energy levels

of different minibands. From a semiclassical point of view, the anticrossings between both minibands correspond to cyclotron orbits of electron states localized in different minibands. In this case, one electron could tunnel from one to the other superlattice minibands.

In the literature, other methods based on the transfer matrix method have been proposed to study the effect of the transverse magnetic field on the superlattice energy spectrum (see e. g. [13,14]). However, these other methods use some analytical solutions of equation (8) in each layer (hypergeometrical confluent functions [13] or parabolic cylinder functions [14]). The numerical calculation of these functions requires long CPU times and introduces numerical errors and instabilities that in our scheme are avoided. Using the analytical method of Ref. [13] to calculate the energy levels for a double barrier structure one needs 10 times longer CPU time than to compute the same structure with the present method with $L = 6$.

IV. THE ENLARGED WELL PROBLEM IN SUPERLATTICES

Recently, Chomette *et al* [21] have proposed to use an enlarged well (EW) as a marker of the arrival of carriers at a certain distance from the surfaces. This method allows to study vertical transport in superlattices by means of optical techniques. Including a well in the superlattice, which is wider than the superlattice wells, introduces a localized state in the energy spectrum. The level due to the EW has a lower energy than the superlattice miniband. In this way, the photoluminescence from the EW can be used as a measure of the transport through the superlattice. [21] In absence of any applied magnetic field, it is found that the original superlattice miniband is slightly affected by the introduction of an EW, so that, the results obtained with this technique can be used to understand the transport through superlattice minibands without an EW. The enlarged well technique has been used to study magnetotransport in superlattice in the cases of $B||z$ [22] and $B\perp z$. [4,23] In this section, we analyze the perturbation of the superlattice energy spectrum due to the EW when an external magnetic field parallel and perpendicular to the growth direction is applied.

For parallel magnetic field, the electron energy levels are easily found through the method of calculation described in section II. Table II reports, for $B=50$ T and $n=0$, the electronic energy levels for a 30/30 $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice and for the same superlattice with an EW of $60\text{\AA}$ in the middle. The electronic energy levels are only slightly changed by the presence of the EW even for this very high B value. Consequently, it is possible to use an EW as a marker to study magnetotransport in superlattices with $B||z$ by means of optical techniques.

For $B\perp z$ and using the method of section III, we show in Fig. 4 and 5 the energy levels for the same superlattices as those used to obtain Fig. 2 and 3 except that a $60\text{\AA}$ and $120\text{\AA}$ EW are introduced in the middle of the 30/30 and 60/60 superlattice, respectively. The introduction of the EW breaks the periodic symmetry of the superlattice and introduces a weaker inversion symmetry respect to the center of the EW. The interaction between the unperturbed dispersion relation of the superlattice and of the EW results in a situation very different from that shown in Fig 2 and 3. In particular, the flat dispersion reminiscent of the electronic miniband becomes dispersive after the introduction of the EW. This is due to the anticrossing between the EW states and the SL states. This perturbation of the SL energy levels disappears far away from the EW region. In a semiclassical point of view,

the anticrossing between the EW energy level and the superlattice miniband corresponds to skipping orbits centered in the barriers on the left and right sides of the EW. [5] One electron in a superlattice state can tunnel to the EW localized state. As a consequence of this interaction, for $B \perp z$, the EW effect on the superlattice energy spectrum should be considered when the EW technique is used to study magnetotransport through a superlattice.

V. DENSITY OF STATES

In quantum wells, the two dimensional density of states, $\rho(E)$, is usually taken as a step function. [24] In a superlattice composed by a finite number of layers, $\rho(E)$ is a series of step, one for each level in the miniband. A parallel magnetic field collapses the 2D energy levels in a discrete set of 0D Landau states. In this case, the step like function for $\rho(E)$ is changed to a discrete set of Dirac δ -functions. [24] Including a Gaussian broadening of the δ -functions caused from the presence of disorder, $\rho(E)$ results

$$\rho(E) = C \sum_m \sum_n \exp\{-[E_m + \hbar\omega_w(n + 1/2) - E]^2/\sigma^2\} \quad (9)$$

where C is a normalization factor, E_m are the energy levels of the superlattice in the z direction with the index m running over the superlattice miniband, n is the Landau level index and σ is the gaussian width. We have neglected the second term on the right hand side of equation (3) to obtain the energy eigenvalues E_m , i.e. to compute equation (9) we have used the E_m values obtained in absence of a magnetic field. Figure 6 reports $\rho(E)$ for a 30/30 superlattice for different magnetic fields. The Landau quantization changes $\rho(E)$ in a set of isolated peaks. For each energy level in the miniband, the distance between two Landau states is given by the cyclotron frequency, $\hbar\omega_w$. Increasing the applied magnetic field, the cyclotron frequency, which is proportional to B , increases, and then, the distance between different peaks.

For $B \perp z$, the density of states is,

$$\rho(E) = \frac{eBL_x}{c} \frac{1}{(2\pi\hbar)^2} \sum_m \int_0^{L_z} \sqrt{\frac{m^*}{2[E - E_m(z_0)]}} \theta[E - E_m(z_0)] dz_0 \quad (10)$$

where $E_m(z_0)$ are the solutions of equation (16) which depend on the cyclotron orbit center z_0 , and L_x , L_z are the superlattice dimension. The square root dependence of $\rho(E)$ is due to the 1D motion in the x -direction which is affected neither by the superlattice potential nor by the magnetic field. A singularity in the denominator of the square root occurs at $E = E_m(z_0)$ and it leads to important modifications in the optical and transport properties of these systems.

Figure 7 shows different $\rho(E)$ computed using eq. (10). For a 60/60 superlattice at $B=4$ T (full line in Fig. 7), the existence of two electronic minibands is observed at about 60 meV and 220 meV. The second electronic minibands is wider than the first one and this allows the resolution of distinct peaks in $\rho(E)$. These peaks show a characteristic $1/\sqrt{E}$ dependency. In Fig. 7, we compare also the $\rho(E)$ results for $B=5$ T of a 30/30 superlattice in presence (solid line) and in absence (dashed line) of a 60 Å EW. In the miniband energy region ($\simeq 150$ meV), the effect of the EW induces a loosening of the 1D typical divergence,

especially for the states near the high energy edge. The direct contribution of two non-dispersive EW eigenvalues in the density of states is marked by two arrows. If the B value is increased no more non-dispersive levels exist and the 1D divergence in the miniband region will disappear.

VI. THE FIBONACCI SUPERLATTICES

Another interesting problem which can be tackled by the present approach is quasi-periodic superlattices. These structures do not exhibit translational invariance but long range order. The interest stems from the fact that the Bloch theorem is inapplicable and that they provide an intermediate class between periodic superlattice with extended electronic states and randomly disordered superlattice with exponentially localized electronic states. Merlin et al. [25] proposed to grow quasi periodic superlattice using the Fibonacci sequence. These superlattices, called Fibonacci superlattices (FSL), are interesting because using a simple recurrent law one can obtain series of increasing period starting from usual simple superlattice and ending with a completely non periodic superlattice. [26–28] We recall that a quasi-periodic FSL of order f is constructed by f applications of the Fibonacci transformation law $A \rightarrow AB$ and $B \rightarrow A$ starting from A , yielding the following sequences: B ($f = -1$), A ($f = 0$), AB ($f = 1$), ABA ($f = 2$), ABAAB ($f = 3$),

In Fig. 8 we show the electronic energy dispersion for different FSL and for B = 0 and B = 5 T. The evolution with the magnetic field strength of the energy level scheme is shown in Fig. 9 for a FSL with index $f=1$ and for B = 0, 1, 3, 5 T. In our calculations, following Ref. [27,16], the block A was formed by 28 Å of *GaAs* and 30.8 Å monolayers of $\text{Al}_{0.23}\text{Ga}_{0.77}\text{As}$, and the block B by 28 Å monolayers of *GaAs* and 67.2 monolayers of $\text{Al}_{0.23}\text{Ga}_{0.77}\text{As}$. We have repeated the Fibonacci series to obtain a total superlattice thickness of $\approx 1000\text{Å}$ for the different FSL but the $f=5$ FSL which has a superlattice thickness of 1500 Å.

For B=0, our method yields the same results as the calculations of Ref. [27,16]. In summary, two kinds of states are formed in the spectrum of a FSL. The first is formed by single-A pattern (typical of $f = 1$ FSL), the second kind is formed by double-A pattern (typical of $f = 2$ FSL). A double-A pattern is analogous of two coupled QW separated by a thick barrier. Little overlap exists between these two kinds of states for the $f = 1$ and the $f = 2$ FSL, whereas the electronic energy spectrum of the other FSL presents overlaps with either the $f = 1$ FSL energy bands or $f = 2$ FSL energy bands (see in Fig. 8 the B=0 T results for $f=3$ or $f=5$). The effect of an external magnetic field is the breaking of this simple scheme. In particular, for $f=0$ (periodic superlattice) and B= 5 T we get non-dispersive states in the region of the superlattice miniband and dispersive states for higher energies. While for $f \neq 0$, almost all the states are dispersive. The quasi-periodicity of the FSL is lost and the energy dispersions are very similar for different f -values. The magnetic field localizes the electronic orbit in finite spatial regions. Hence the electron are subject to the local potential (V_{eff}). V_{eff} does not show the quasi periodicity of the Fibonacci superlattice potential. This fact is shown in Fig. 9 for $f=1$. By decreasing the electron cyclotronic orbit (i. e. increasing B) increases the dispersion of the states. For B=1 T the energy dispersion is flat. Increasing the magnetic field the energy dispersion changes: for B=3 T we observe both dispersive and non dispersive states while for B=5 T almost all the states are dispersive. We note that the band of states at $\approx 250\text{-}300$ meV which develops for B= 5

T and for $f=0-3$ in Fig. 8 is due to the finite size of the superlattices.

VII. SUMMARY

In summary, we have presented a simple method to compute the effect of an external magnetic field on the energy spectrum of superlattices. This method is based on the transfer matrix approach. Due to the strong non-parabolicity and the valence band mixing of hole states in superlattices, we have applied our approach only to the electronic states in this paper.

A magnetic field parallel to z leads to a full quantization of the electronic motion in the layer plane. The conservation of the Landau level indexes along the superlattice increases the energy miniband width and induces a dependence of the energy levels on the Landau index and the applied magnetic field value. The density of states is changed from a step-like function to a set of δ -like functions.

For $B \perp z$ case, we have computed the dispersion relations and the density of states for electrons in a superlattice. The energy spectrum shows the existence of energy regions with dispersive and non dispersive energy states. The density of states is characterized by a typical $1/\sqrt{E}$ dependency for non-dispersive states and by a smooth increase for dispersive states.

We have applied our method to study the enlarged well problem in superlattices with an applied magnetic field. With $B \parallel z$, we have found that the presence of the EW is only a small perturbation on the superlattice energy spectrum which permits the use an EW in the study of magnetotransport through superlattices. For $B \perp z$ case, the EW strongly perturbs the superlattice energy spectrum.

Fibonacci superlattices which are a particular class of non-periodic structures show some interesting aspects due to the loss of the quasi-periodicity in magnetic fields. Our preliminary results suggest that due to the increase of the magnetic localization of the electrons the self-similar energy spectrum typical of these quasi-periodic structure is lost. A magnetic field of 5 T is enough to render dispersive all the electronic states while for periodic superlattice the energy dispersion is still flat at this value of the magnetic field.

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TRANSFER MATRIX METHOD

Through the effective-mass approach it is possible to separate the wave function in a component parallel to the layers and a component in the growth direction, z . The eigenvalues in the z direction, E_z , and the envelope wave functions, $\psi(z)$, in a superlattice can be calculated using spherical masses and parabolic dispersions in the layer plane. [29,30] In this way, the motion of electrons and holes in the growth direction can be decoupled and reduced to the solution of a one-dimensional Schrödinger equation for each kind of particle. Let us assume to solve the problem of electrons. The Schrödinger equation is:

$$\left[-\frac{\hbar^2}{2m^*(z)} \nabla^2 + V_{SL}(z) \right] \psi(z) = E\psi(z) \quad (11)$$

where m^* is the effective mass for electrons in the different semiconductor layers and $V_{SL}(z)$ is the superlattice potential. The superlattice potential is given by the difference of the energy gap between different layers which we have approximated using a one dimensional *Kronig-Penney*-like potential. [31] The energy zero is defined at the bottom of the GaAs conduction band for the electrons. The envelope wave function solution of (11) in the i th well is

$$\psi_i(z) = A_i \cos(k_i z) + B_i \frac{m_i^*}{k_i} \sin(k_i z) \quad (12)$$

where A_i and B_i are two constants, $k_i = (2m_i^* E)^{1/2}/\hbar$ and m_i^* is the effective mass in the i th layer. The envelope wave function in a i th barrier is

$$\psi_i(z) = \frac{A_i}{\sqrt{2}} e^{-\kappa_i z} + \frac{B_i}{\sqrt{2}} \frac{m_i^*}{\kappa_i} e^{\kappa_i z} \quad (13)$$

where $\kappa_i = \sqrt{2m_i^*(V_0 - E)}/\hbar$, with V_0 as the height of the potential barrier.

Using a carrier current conserving boundary condition, the continuity of $\psi(z)$ and $\psi'(z)/m^*$, the coefficients A_i and B_i of the layer i are joined to those of the layer $i+1$ by a transfer 2x2 matrix $\mathcal{S}_{i \rightarrow i+1}$ of determinant 1 defined in the following way [16]

$$\begin{pmatrix} A_{i+1} \\ B_{i+1} \end{pmatrix} = \mathcal{S}_{i \rightarrow i+1} \begin{pmatrix} A_i \\ B_i \end{pmatrix} \quad (14)$$

$\mathcal{S}_{i \rightarrow i+1}$ is equal to $(C_{i+1}^w)^{-1} C_i^b$ if the layer i is a barrier and the $(i+1)$ th layer a well, and to $(C_{i+1}^b)^{-1} C_i^w$ if the i th layer is a well and the $(i+1)$ th layer a barrier. Both functions C are calculated at the interface between the i and $(i+1)$ layer. C_i^w is defined as

$$C_i^w = \begin{pmatrix} \cos(k_i z) & \frac{m_i^*}{k_i} \sin(k_i z) \\ \frac{-\kappa_i}{m_i^*} \sin(k_i z) & \cos(k_i z) \end{pmatrix} \quad (15)$$

and C_i^b as

$$C_i^b = \begin{pmatrix} e^{-\kappa_i z} & \frac{m_i^*}{\kappa_i} e^{\kappa_i z} \\ \frac{-\kappa_i}{m_i^*} e^{-\kappa_i z} & e^{\kappa_i z} \end{pmatrix} \quad (16)$$

By consecutive applications of the matrix $\mathcal{S}_{i \rightarrow i+1}$ we form the matrix $\mathcal{M}$ which joins the first and last layers of the superlattice

$$\begin{pmatrix} A_N \\ B_N \end{pmatrix} = \mathcal{M} \begin{pmatrix} A_1 \\ B_1 \end{pmatrix} = \prod_{i=N}^2 \mathcal{S}_{i-1 \rightarrow i} \begin{pmatrix} A_1 \\ B_1 \end{pmatrix} \quad (17)$$

with N the number of superlattice layers. Imposing vanishing wavefunctions in the first and last superlattice layers, we find that $A_1 = B_N = 0$, and from (17) the (2,2) element of the matrix $\mathcal{M}$ results in

$$\mathcal{M}_{22} = 0 \tag{18}$$

The solutions of the eigenvalue equation (18) yield the miniband spectrum for electrons in the superlattice.

This method, which use the product of 2x2 matrices, can be easily implemented on small computers and it permits to calculate any finite succession of layers and not only periodic superlattices. On the other hand, we neglect energy band non-parabolicity for the electrons and the heavy-hole light-hole mixing in the valence band. Consequently a big error is expected when these effects are important. To estimate the errors on our calculations, we have compared our results with the ones of Ref. [24] where energy band non-parabolicity and valence band mixing have been considered. The differences between the results for short period superlattices (period shorter than 120 Å) are of about 2% for electron energy levels and of about 10% for hole energy levels. Due to the neglect of valence band mixing, we have found a worst agreement for the heavy hole energies than for electron energies, where the agreement is rather satisfying. To go beyond our approximations, larger matrices are necessary, [32] which result in a larger computational effort.

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band gap $(1.5192 + 1.247 x)$ eV, electron effective mass $(0.067 + 0.083 x) m_o$, heavy hole effective mass $(0.45 + 0.31 x) m_o$, light hole effective mass $(0.082 + 0.083 x) m_o$,
band offset $\Delta E_c = 0.62\Delta E_g$ (where ΔE_g and ΔE_c are the band gap and conduction band discontinuities between GaAs and $\text{Al}_x\text{Ga}_{1-x}\text{As}$).
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FIGURES

FIG. 1. Lowest and highest electronic energy level in the miniband of a 30/30 (30 Å wide wells and barriers) $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice versus the applied parallel magnetic field B for different Landau level index. Solid line: $n=0$, Dotted line: $n=1$, Dashed line: $n=2$. The zero of the energy scale is the bottom of the GaAs conduction band.

FIG. 2. Solid line: electron dispersion relation for the 30/30 (30 Å wide wells and barriers) $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice for a perpendicular magnetic field $B=5\text{T}$. Dashed line: position of the equivalent superlattice potential. The zero of the energy scale is the bottom of the GaAs conduction band.

FIG. 3. Solid line: electron dispersion relation for the 60/60 (60 Å wide wells and barriers) $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice for a perpendicular magnetic field $B=4\text{T}$. Dashed line: position of the equivalent superlattice potential. The zero of the energy scale is the bottom of the GaAs conduction band.

FIG. 4. Solid line: electron dispersion relation for the 30/30 (30 Å wide wells and barriers) $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice with a 60Å enlarged well in the middle, for a perpendicular magnetic field $B=4\text{T}$. Dashed line: position of the equivalent superlattice potential. The zero of the energy scale is the bottom of the GaAs conduction band.

FIG. 5. Solid line: electron dispersion relation for the 60/60 (60 Å wide wells and barriers) $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice with a 120Å enlarged well in the middle, for a perpendicular magnetic field $B=6\text{T}$. Dashed line: position of the equivalent superlattice potential. The zero of the energy scale is the bottom of the GaAs conduction band.

FIG. 6. Density of states in arbitrary units versus energy for a 30/30 (30 Å wide wells and barriers) $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice in a parallel magnetic field. Solid line: $B=1\text{T}$. Dashed line: $B=2.5\text{T}$. The zero of the energy scale is the bottom of the GaAs conduction band.

FIG. 7. Density of states versus energy for a 60/60 (60 Å wide wells and barriers) $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ -GaAs superlattice (solid line) at $B=4\text{T}$. The density of states for a 30/30 superlattice is also shown for $B=5\text{T}$ without (solid line) and with (dashed line) an enlarged well in the middle. The magnetic field is perpendicular to the growth axis. The zero of the energy scale is the bottom of the GaAs conduction band. The arrows indicate the enlarged well bound states.

FIG. 8. Electronic energy levels of different Fibonacci superlattices with index f as a function of the cyclotronic orbit center (z_o) for a perpendicular magnetic field $B=0\text{ T}$ (discs) and $B=5\text{ T}$ (points). For a definition of the Fibonacci index f and for the superlattice parameters see the text. For $B=0\text{ T}$ the energy levels do not depend on z_o . The energy barrier in the superlattice is 177 meV and the zero of the energy scale is the bottom of the GaAs conduction band.

FIG. 9. Electronic energy levels of a Fibonacci superlattice with index $f=1$ as a function of the cyclotron orbit center z_o and for different values of the perpendicular magnetic field B . For $B=0$ T the energy levels do not depend on z_o . For a definition of the Fibonacci index f and for the superlattice parameters see the text. The energy barrier in the superlattice is 177 meV and is indicated in the figure by an horizontal line. The zero of the energy scale is the bottom of the GaAs conduction band.

TABLES

TABLE I. First seven electron eigenvalues for 20 coupled quantum wells (30/30 superlattice) with $B=5T$ at different L values. The cyclotron orbit center value has been taken in the middle of the sample. The zero of the energy scale is the bottom of the GaAs conduction band.

Electron energy levels (meV)							
L=1	106.84	114.11	121.26	128.29	135.15	141.81	148.18
L=2	104.13	113.20	119.32	126.27	134.13	139.24	145.28
L=3	103.93	113.02	118.92	125.69	133.55	138.45	144.93

TABLE II. First seven superlattice eigenvalues for 20 coupled quantum wells (30/30 superlattice) with $B||z$ and for the same superlattice potential with an implemented EW. The magnetic field is $B=50T$ and Landau level index is $n=0$. The zero of the energy scale is the bottom of the GaAs conduction band.

Electron energy levels (meV)							
SL	97.97	98.67	99.83	101.46	103.52	106.03	108.95
EW	96.23	97.32	98.51	99.62	102.12	105.81	107.41